

SGH80N60UF

Ultra-Fast IGBT

General Description

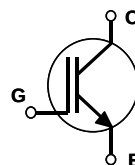
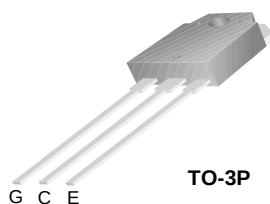
Fairchild's UF series of Insulated Gate Bipolar Transistors (IGBTs) provides low conduction and switching losses. The UF series is designed for applications such as motor control and general inverters where high speed switching is a required feature.

Features

- High speed switching
- Low saturation voltage : $V_{CE(sat)} = 2.1 \text{ V @ } I_C = 40\text{A}$
- High input impedance

Applications

AC & DC motor controls, general purpose inverters, robotics, and servo controls.



Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Description	SGH80N60UF	Units
V_{CES}	Collector-Emitter Voltage	600	V
V_{GES}	Gate-Emitter Voltage	± 20	V
I_C	Collector Current @ $T_C = 25^\circ\text{C}$	80	A
	Collector Current @ $T_C = 100^\circ\text{C}$	40	A
$I_{CM(1)}$	Pulsed Collector Current	220	A
I_F	Diode Continuous Forward Current @ $T_C = 100^\circ\text{C}$	25	A
I_{FM}	Diode Maximum Forward Current	280	A
P_D	Maximum Power Dissipation @ $T_C = 25^\circ\text{C}$	195	W
	Maximum Power Dissipation @ $T_C = 100^\circ\text{C}$	78	W
T_J	Operating Junction Temperature	-55 to +150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_L	Maximum Lead Temp. for Soldering Purposes, 1/8" from Case for 5 Seconds	300	$^\circ\text{C}$

Notes :

(1) Repetitive rating : Pulse width limited by max. junction temperature

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	--	0.64	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	--	40	$^\circ\text{C/W}$

Electrical Characteristics of the IGBT T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
Off Characteristics						
BV _{CES}	Collector-Emitter Breakdown Voltage	V _{GE} = 0V, I _C = 250uA	600	--	--	V
ΔB _V _{CES} /ΔT _J	Temperature Coefficient of Breakdown Voltage	V _{GE} = 0V, I _C = 1mA	--	0.6	--	V/°C
I _{CES}	Collector Cut-Off Current	V _{CE} = V _{CES} , V _{GE} = 0V	--	--	250	uA
I _{GES}	G-E Leakage Current	V _{GE} = V _{GES} , V _{CE} = 0V	--	--	± 100	nA
On Characteristics						
V _{GE(th)}	G-E Threshold Voltage	I _C = 40mA, V _{CE} = V _{GE}	3.5	4.5	6.5	V
V _{CE(sat)}	Collector to Emitter Saturation Voltage	I _C = 40A, V _{GE} = 15V	--	2.1	2.6	V
		I _C = 80A, V _{GE} = 15V	--	2.6	--	V
Dynamic Characteristics						
C _{ies}	Input Capacitance	V _{CE} = 30V, V _{GE} = 0V, f = 1MHz	--	2790	--	pF
C _{oes}	Output Capacitance		--	350	--	pF
C _{res}	Reverse Transfer Capacitance		--	100	--	pF
Switching Characteristics						
t _{d(on)}	Turn-On Delay Time	V _{CC} = 300 V, I _C = 40A, R _G = 5Ω, V _{GE} = 15V, Inductive Load, T _C = 25°C	--	23	--	ns
t _r	Rise Time		--	50	--	ns
t _{d(off)}	Turn-Off Delay Time		--	90	130	ns
t _f	Fall Time		--	50	150	ns
E _{on}	Turn-On Switching Loss		--	570	--	uJ
E _{off}	Turn-Off Switching Loss	V _{CC} = 300 V, I _C = 40A, R _G = 5Ω, V _{GE} = 15V, Inductive Load, T _C = 125°C	--	590	--	uJ
E _{ts}	Total Switching Loss		--	1160	1500	uJ
t _{d(on)}	Turn-On Delay Time		--	30	--	ns
t _r	Rise Time		--	55	--	ns
t _{d(off)}	Turn-Off Delay Time		--	150	200	ns
t _f	Fall Time	V _{CE} = 300 V, I _C = 40A, V _{GE} = 15V	--	160	250	ns
E _{on}	Turn-On Switching Loss		--	630	--	uJ
E _{off}	Turn-Off Switching Loss		--	940	--	uJ
E _{ts}	Total Switching Loss		--	1580	2000	uJ
Q _g	Total Gate Charge		--	175	250	nC
Q _{ge}	Gate-Emitter Charge	Measured 5mm from PKG	--	25	40	nC
Q _{gc}	Gate-Collector Charge		--	60	90	nC
L _e	Internal Emitter Inductance		--	14	--	nH

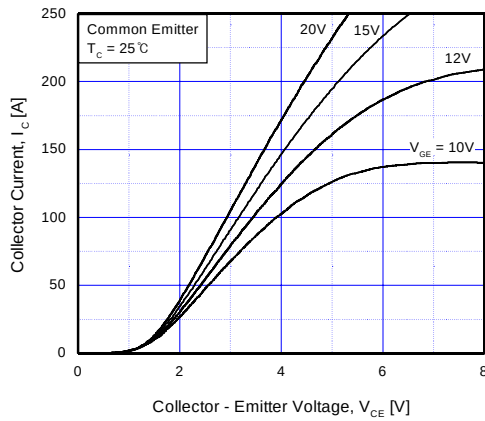


Fig 1. Typical Output Characteristics

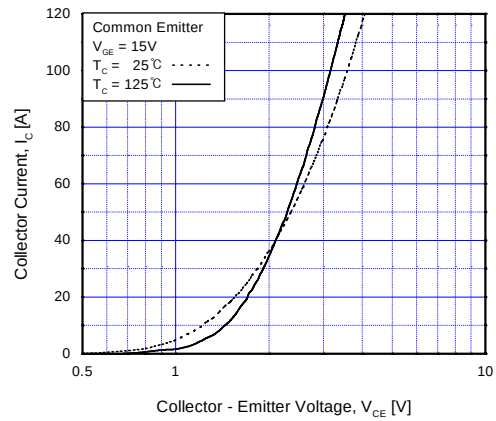


Fig 2. Typical Saturation Voltage Characteristics

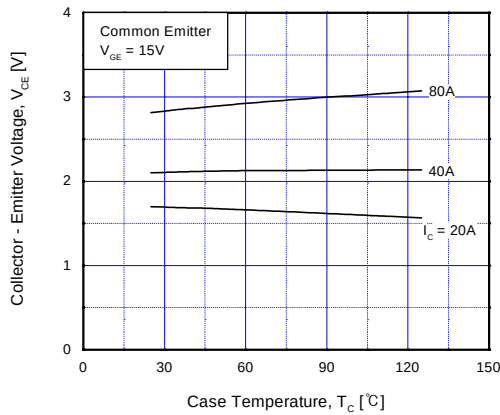


Fig 3. Saturation Voltage vs. Case Temperature at Variant Current Level

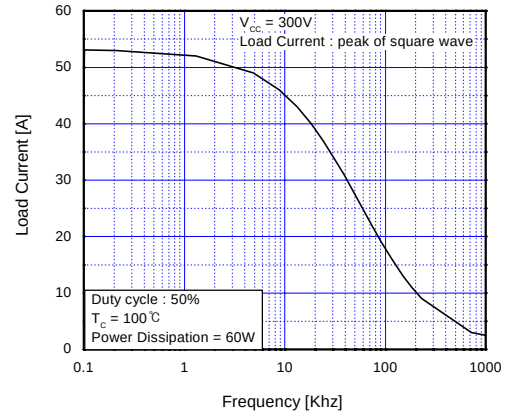


Fig 4. Load Current vs. Frequency

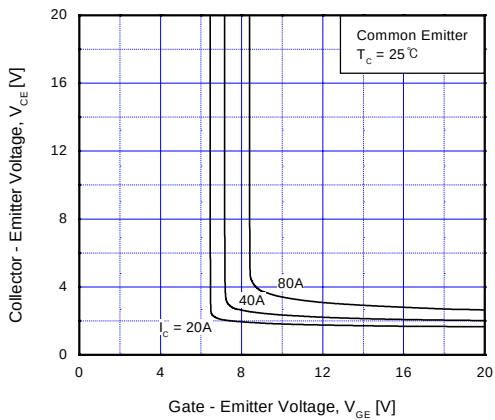


Fig 5. Saturation Voltage vs. V_{GE}

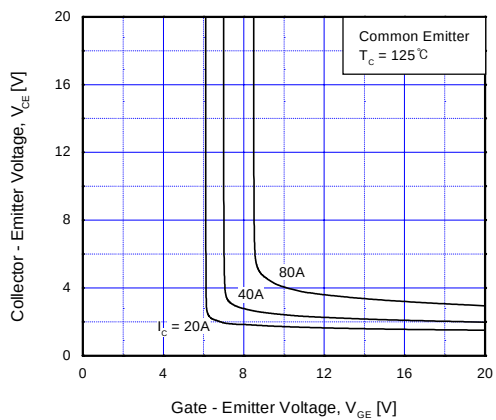


Fig 6. Saturation Voltage vs. V_{GE}

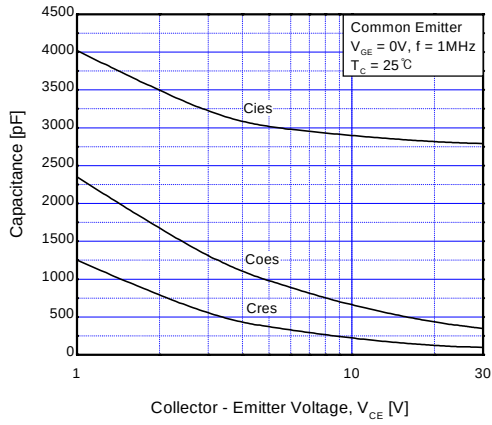


Fig 7. Capacitance Characteristics

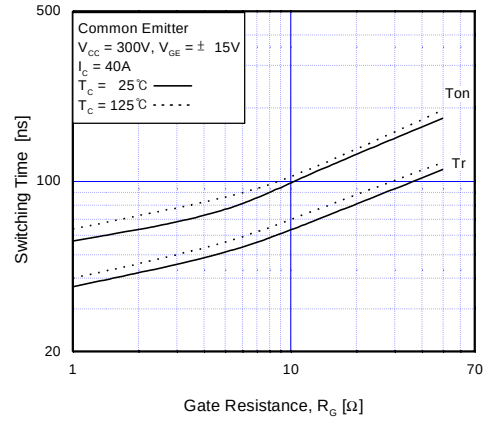


Fig 8. Turn-On Characteristics vs. Gate Resistance

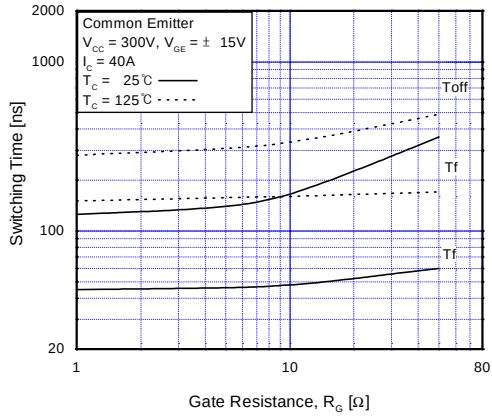


Fig 9. Turn-Off Characteristics vs. Gate Resistance

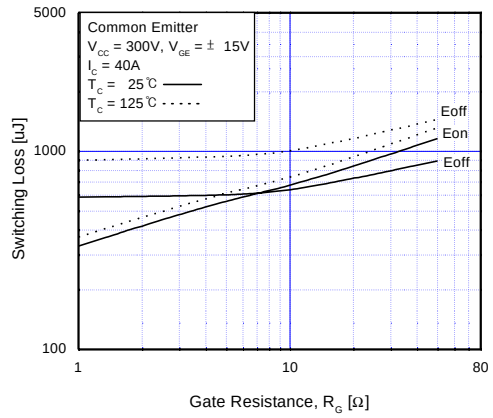


Fig 10. Switching Loss vs. Gate Resistance

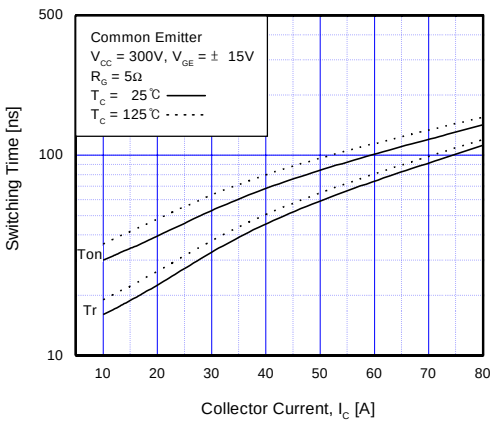


Fig 11. Turn-On Characteristics vs. Collector Current

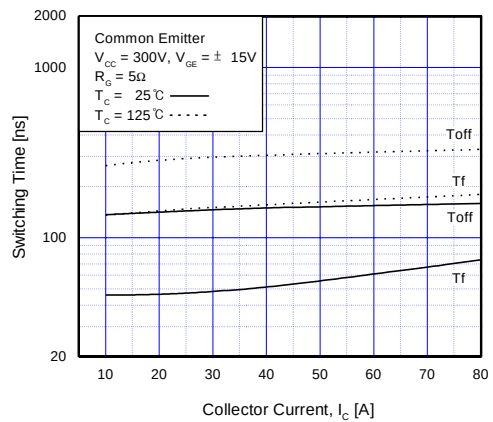


Fig 12. Turn-Off Characteristics vs. Collector Current

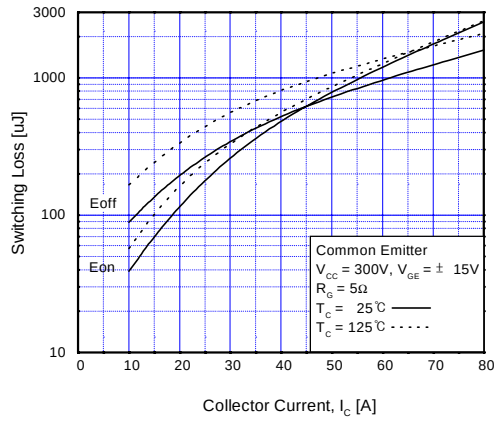


Fig 13. Switching Loss vs. Collector Current

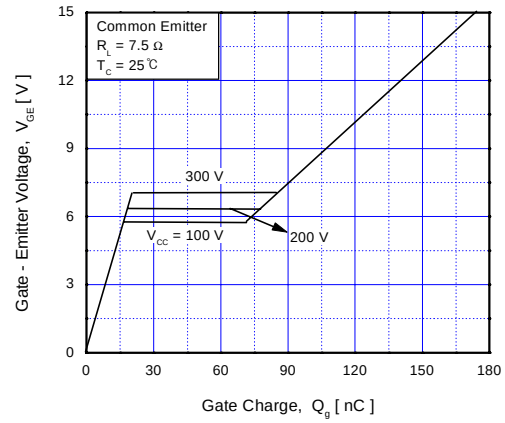


Fig 14. Gate Charge Characteristics

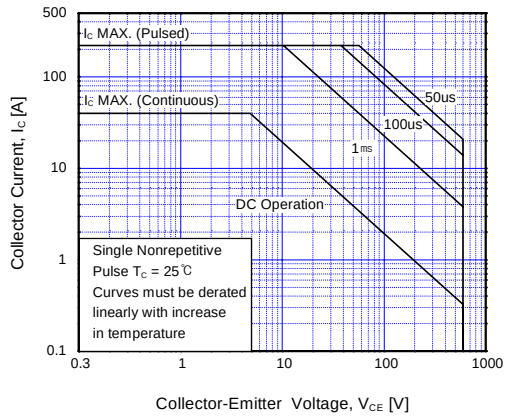


Fig 15. SOA Characteristics

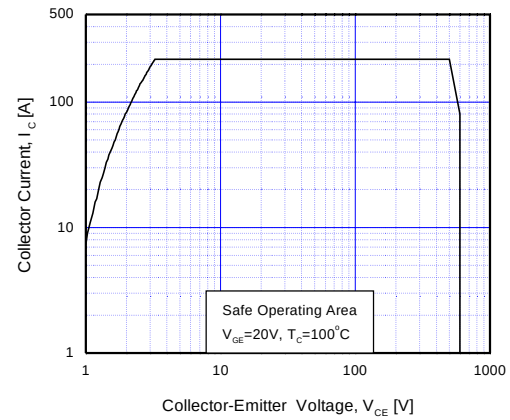


Fig 16. Turn-Off SOA Characteristics

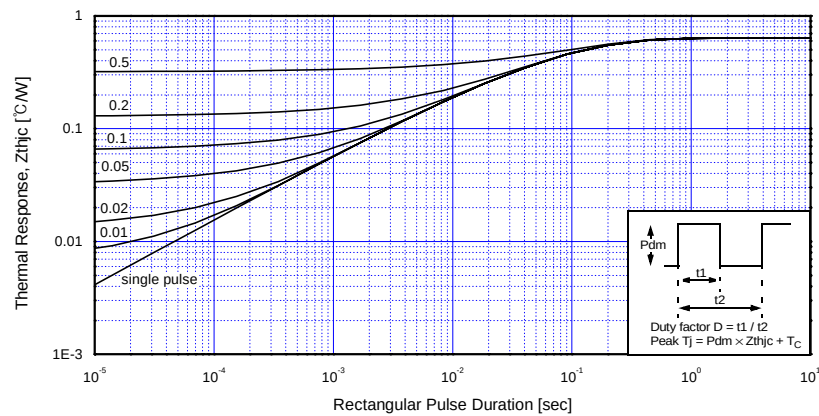
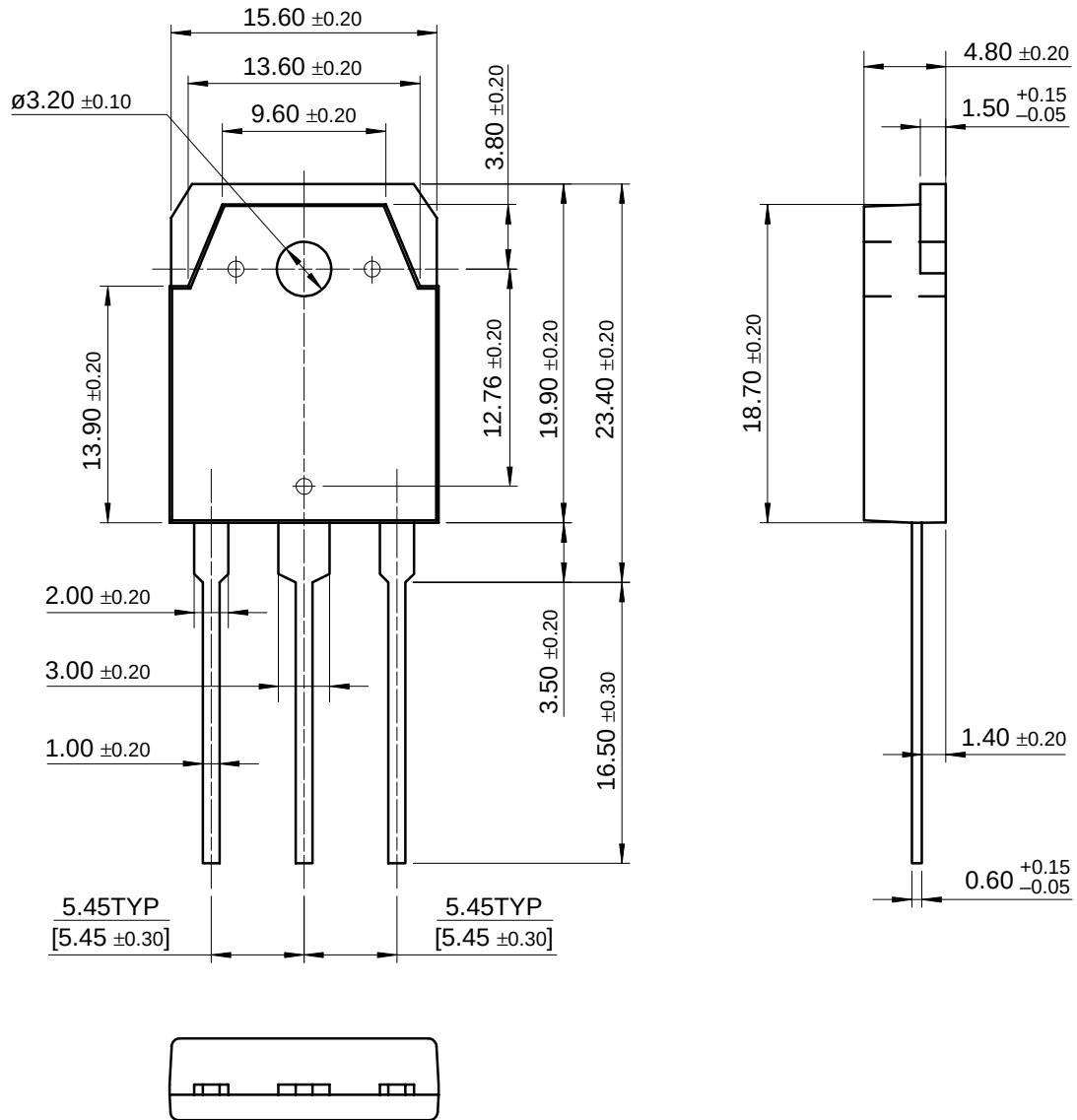


Fig 17. Transient Thermal Impedance of IGBT

Package Dimension

TO-3P



Dimensions in Millimeters

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